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Amendments to Claims

IN THE CLAIMS:

1. (Currently amended) A light-emitting device comprising: an anode comprising a semi-transparent layer having a high reflectivity and a high work function, wherein the semi-transparent layer has a reflectivity of at least 86%; and

a cathode comprising at least one first cathode layer of a low work function material selected from metal, metal oxide and combinations thereof, and at least one second cathode layer having a high reflectivity and a high work function.

at least one emissive layer disposed between the anode and first cathode layer wherein the emissive layer is in contact with the first cathode layer,

wherein said device is a metal etalon microcavity structure.

- 2. (Original) The device of Claim 1, wherein the semi-transparent layer has a work function of greater than 4 eV.
- 3. (Original) The device of Claim 1, wherein the semi-transparent layer includes an anode material selected from metals and metal alloys.
- 4. (Original) The device of Claim 1, wherein the second cathode layer has a work function of greater than 4 eV.
- 5. (Original) The device of Claim 1, wherein the second cathode layer includes a cathode material selected from metals and metal alloys.
- 6. (Original) The device of Claim 1 wherein the semi-transparent layer has a reflectivity of at least 91.4% at the wavelength of emission.
- 7. (Original) The device of Claim 1 wherein the semi-transparent layer has a reflectivity of more than about 92% at the wavelength of emission.
- 8. (Original) The device of Claim 1 wherein the semi-transparent layer has a reflectivity of from 92 to 96.5% at the wavelength of emission.
- 9. (Original) The device of Claim 1 wherein the semi-transparent layer has a reflectivity of from 94 to 96.5% at the wavelength of emission.
- 10. (Original) The device of Claim 1 wherein the semi-transparent layer has a reflectivity of more than about 96% at the wavelength of emission.
 - 11. (Canceled)
- 12. (Original) The device of Claim 1 wherein the semi-transparent layer comprises silver.
- 13. (Original) The device of Claim 1 wherein the at least one second cathode layer comprises silver.
- 14. (Original) The device of Claim 1 wherein the at least one second cathode layer has reflectivity of at least 91.4% at the wavelength of emission.

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15. (Original) The device of Claim 1 wherein the at least one second cathode layer has reflectivity of between about 92 and 96.5% at the wavelength of emission.

- 16. (Original) The device of Claim 1 wherein the at least one second cathode layer has reflectivity of between about 94 to 96.5 % at the wavelength of emission.
- 17. (Original) The device of Claim 1 wherein the at least one second cathode layer has reflectivity of greater than about 96% at the wavelength of emission.
- 18. (Original) The device of Claim 1 wherein the at least one second cathode layer includes a layer of air-stable metal coated on a silver layer.
 - 19. (Original) The device of Claim 1 wherein:

the semi-transparent layer has a first surface adjacent to the cathode and an opposite second surface:

the anode further comprising a passivation layer adjacent to the first surface, the passivation layer comprising a passivation material selected from poly(aniline), poly(aniline) blends, polythiophene, and polythiophene blends.

- 20. (Original) The device of Claim 1 wherein the semi-transparent layer has a thickness of from about 100 up to 500 Å.
- 21. (Original) The device of Claim 1 wherein the semi-transparent layer has a thickness of from about 250 up to 400 Å.
- 22. (Original) The device of Claim 1 wherein the semi-transparent layer has a thickness of from about 275 up to 350 Å.
- 23. (Original) The device of Claim 1 wherein the semi-transparent layer has a thickness of from about 275 up to 325 Å.
 - 24. (Original) The device of Claim 1, wherein:

the semi-transparent layer has a first surface adjacent to the cathode and an opposite second surface;

the anode further comprises a transparent layer of indium/tin oxide adjacent to the second surface of the semi-transparent layer.